

L Number	Hits	Search Text	DB	Time stamp
1	2315	438/636,637,700,725.ccls.	USPAT; US-PGPUB	2002/11/18 09:33
2	1638	438/636,637,700,725.ccls. and @ad<=19991102	USPAT; US-PGPUB	2002/11/18 09:33
3	261	(438/636,637,700,725.ccls. and @ad<=19991102) and (ARC or (anti adj reflective))	USPAT; US-PGPUB	2002/11/18 09:26
4	83	438/749.ccls.	USPAT; US-PGPUB	2002/11/18 09:33
5	55	438/749.ccls. and @ad<=19991102	USPAT; US-PGPUB	2002/11/18 09:34

	U	1 [1]	Document ID	Issue Date	Pages
1	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20010046791 A1	20011129	7
2	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6475904 B2	20021105	17
3	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6352937 B1	20020305	7
4	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6191046 B1	20010220	10
5	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6156640 A	20001205	10
6	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6127259 A	20001003	7
7	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 6057239 A	20000502	7

	Title	Current OR	Current XRef
1	USE OF SILICON OXYNITRIDE ARC FOR METAL LAYERS	438/786	438/636; 438/69; 438/72
2	Interconnect structure with silicon containing alicyclic polymers and low-k dielectric materials and method of making same with single and dual damascene techniques	438/637	430/313; 430/317; 438/638
3	Method for stripping organic based film	438/725	216/67; 438/737
4	Deposition of an oxide layer to facilitate photoresist rework on polygate layer	438/723	438/724; 438/725
5	Damascene process with anti-reflection coating	438/636	438/618; 438/620; 438/622; 438/629
6	Phosphoric acid process for removal of contact BARC layer	438/626	438/631; 438/636; 438/645
7	Dual damascene process using sacrificial spin-on materials	438/689	438/695; 438/700; 438/704; 438/710; 438/745